

Semiconductor Surfaces and Interfaces

Their Atomic and Electronic Structures

by
Friedhelm Bechstedt / Rolf Enderlein

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CONTENTS

INTRODUCTION

CHAPTER 1

FUNDAMENTALS

1

1.1.	Atomic structure of three-dimensional crystals	1
1.1.1.	Lattices, point and space group symmetries	1
1.1.2.	Lattice planes	5
1.2.	Ideal crystal surfaces	9
1.2.1.	Translational symmetry and the lattice of ideal crystal surfaces	10
1.2.2.	Point and space symmetry of ideal crystal surfaces	15
1.2.3.	Projection of a three-dimensional crystal onto its surface	23
1.3.	Relaxed and reconstructed surfaces	31
1.3.1.	Surface induced atomic displacements	31
1.3.2.1.	Translational symmetry	34
1.3.2.2.	Point and space symmetries	39
1.4.	Surface structure and chemical bonding	41
1.4.1.	Bulk crystals	43
1.4.1.1..	Different types of bonding	43
1.4.1.2.	Relation to crystal structure	44
1.4.2.	Bonding at surfaces	47
1.4.2.1.	General aspects	47
1.4.2.2.	Covalent bonding	49
1.4.2.3.	Ionic bonding	54
1.5.	Experimental techniques for the preparation of surfaces and the investigation of their atomic structure	55
1.5.1.	Preparation of surfaces	55
1.5.2.	Experimental techniques for determining surface structure	60
1.5.2.1.	Low energy electron diffraction (LEED)	62
1.5.2.2.	Other methods	66
	References to Chapter 1	69

THEORETICAL METHODS	72
2.1. One-electron Schrödinger equation and its properties in the case of crystal surfaces	72
2.1.1. One-electron approximation	72
2.1.2. Translational symmetry	75
2.1.3. Point and space group symmetries	80
2.1.4. Projection of the bulk energy bands into the first surface BZ	86
2.2. The one-dimensional model of a crystal surface, Tamm and Shockley states	91
2.2.1. Infinite one-dimensional crystal	93
2.2.1.1. Nearly-free-electron approximation	93
2.2.1.2. Complex bandstructure	95
2.2.2. Semi-infinite one-dimensional crystal. Matching	96
2.3. Self-consistent pseudopotential calculations of one-electron states	99
2.3.1. Pseudopotential concept	99
2.3.2. Plane wave expansion	103
2.3.3. Application to surfaces: Matching and periodic slab method	106
2.3.4. Example: Si(111) surface	108
2.4. Tight-binding theory of surface states	113
2.4.1. Foundations of the method	113
2.4.2. Bulk ETBM Hamiltonian	116
2.4.2.1. Basic assumptions	116
2.4.2.2. Slater-Koster ansatz	119
2.4.2.3. Hirabayashi notation	123
2.4.2.4. Wedaire-Thorpe and bond-orbital model	126
2.4.3. Layer-orbital representation	131
2.4.4. Techniques for dealing with the surface geometry problem	133
2.4.4.1. Slab method	133
2.4.4.2. Cluster method	134
2.4.4.3. Transfer-matrix method	135
2.4.4.4. Scattering-theoretic method	136
2.4.5. Scattering-theoretic formalism for surfaces	137
2.4.5.1. General results	137
2.4.5.2. Bulk Green's function	140
2.4.5.3. Perturbation potential for ideal surfaces	141
2.4.6. Applications	144
2.4.6.1. (111) and (100) ideal surfaces of diamond-type crystals	144

2.4.6.2.	Chemisorption on a diamond-type (111) surface	148
2.4.6.3.	Ideal Ge-GaAs(111) interface	151
2.4.7.	Beyond ETBM. Inclusion of self-consistency by means of charge-dependent tight-binding treatment	156
2.5.	Total-energy calculations	159
2.5.1.	Self-consistent pseudopotential calculations in the framework of the local density approximation	160
2.5.2.	Tight-binding methods	164
2.5.2.1.	Charge-self-consistent tight-binding method	165
2.5.2.2.	Force-constant model of Chadi	175
	References to Chapter 2	178

CHAPTER 3

	SURFACES	187
3.1.	Silicon	191
3.1.1.	Silicon (111) surfaces	193
3.1.1.1.	1x1 cells	194
3.1.1.2.	2x1 cells: Buckling, chains, or molecules?	198
3.1.1.3.	7x7 cells	212
3.1.2.	Silicon (100) surfaces	224
3.1.2.1.	2x1 reconstruction: Symmetric and asymmetric dimers or other structure elements?	225
3.1.2.2.	Atomic structure studies	227
3.1.2.3.	Electronic structure	229
3.1.3.	Other silicon surfaces	233
3.2.	Germanium	236
3.2.1.	(111) faces	237
3.2.1.1.	Phases	237
3.2.1.2.	Atomic structure	238
3.2.1.3.	Electronic states	241
3.2.2.	(100) and other faces.	244
3.3.	Diamond	246
3.3.1.	Geometry	246
3.3.2.	Electronic states	248
3.4.	Gallium arsenide	250
3.4.1.	(110) surfaces	251
3.4.1.1.	Relaxation	251
3.4.1.2.	Surface states	255
3.4.2.	Polar surfaces. Prototypes of reconstruction	257
3.4.2.1.	Variety of reconstructions	258

3.4.2.2.	Similarities in electronic structures?	262
3.4.3.	Beyond low indices	267
3.5.	Other zincblende semiconductors. Chemical trends	269
3.5.1.	(110) cleavage faces	269
3.5.1.1.	Atomic structure parameters	269
3.5.1.2.	Gap states?	273
3.5.1.3.	Ionization energies	276
3.5.2.	Other faces	280
3.6.	Wurtzite materials. Prototype: ZnO	282
3.6.1.	Nonpolar (10 $\bar{1}$ 0) and (11 $\bar{2}$ 0) surfaces	283
3.6.2.	Polar (0001) and (000 $\bar{1}$) surfaces	286
	References to Chapter 3	289

CHAPTER 4

INTERFACES	311	
4.1.	Metal-semiconductor interfaces	311
4.1.1.	Historical preliminaries	311
4.1.2.	Phenomenological models	314
4.1.2.1.	Ideal Schottky barrier	314
4.1.2.2.	Real-structure effects. Role of surface states	315
4.1.2.3.	Validity of simple models. Chemical trends	318
4.1.3.	Microscopic concepts	324
4.1.3.1.	Unified defect model	324
4.1.3.2.	"Canonical" Schottky barrier heights. The role of metal-induced gap states	334
4.1.3.3.	Unified disorder-induced gap state model	339
4.1.4.	Interface chemistry and physical properties	342
4.1.4.1.	Elemental semiconductors. Silicon	342
4.1.4.2.	III-V compound semiconductors: GaAs and InP	355
4.2.	Semiconductor-semiconductor interfaces	364
4.2.1.	Shockley-Anderson model	364
4.2.1.1.	Band alignment and electron affinity rule	364
4.2.1.2.	Limitations	368
4.2.2.	Band discontinuities	371
4.2.2.1.	Estimates in framework of the electron affinity rule	372
4.2.2.2.	Interface dipoles	377
4.2.2.3.	Relation to Fermi-level pinning	381
4.2.2.4.	Atomic reference levels	383
4.2.2.5.	Influence of lattice misfit. Band offsets for Si-Si _{1-x} Ge _x	386

4.2.3.	A prototype heterojunction interface: GaAs-Ga _{1-x} Al _x As(100)	391
4.2.3.1.	Scope	391
4.2.3.2.	Interface atomic arrangement	393
4.2.3.3.	Electronic energy spectrum	396
4.3.	Insulator-semiconductor interface: Initial stages of oxide formation	399
4.3.1.	Oxygen onto Si(111) and (100) surfaces	400
4.3.1.1.	Chemisorption	400
4.3.1.2.	Interface region between Si and SiO ₂	404
4.3.2.	Oxygen onto GaAs surfaces	408
4.3.2.1.	Nonpolar (110) cleavage face	408
4.3.2.2.	Polar faces	412
	References to Chapter 4	413
	GLOSSARY OF ACRONYMS	434
	PRINCIPAL SYMBOLS	435
	INDEX	437